

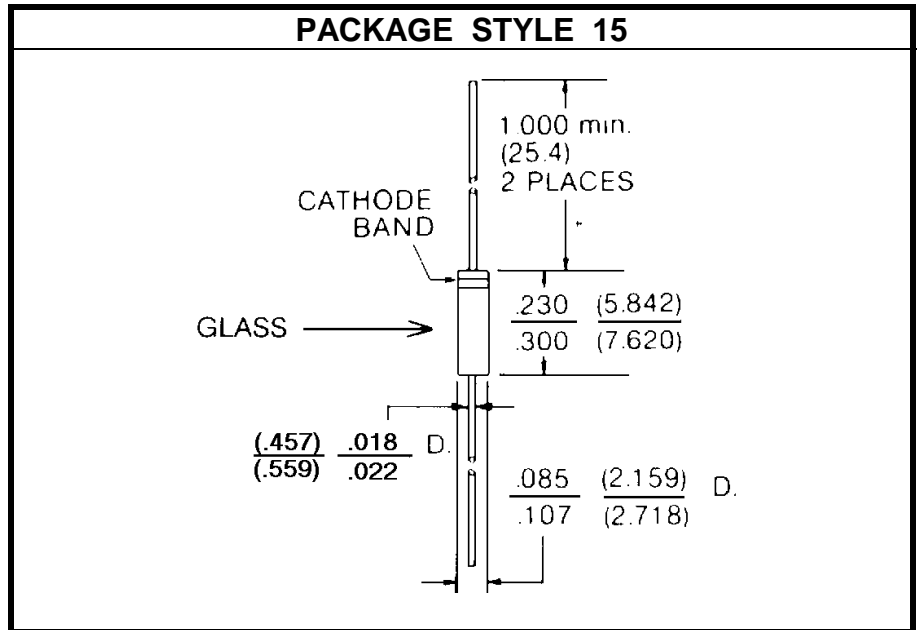
SILICON PIN DIODE

DESCRIPTION:

The **AP1000A** is a Diffused Epitaxial Silicon PIN Diode.

MAXIMUM RATINGS

| | |
|-------------------------|---------------------------------|
| I_C | 100mA |
| V_{CE} | 100 V |
| P_{DISS} | 500 mW @ T _C = 25 °C |
| T_J | -65 °C to +150 °C |
| T_{STG} | -65 °C to +175 °C |
| θ_{JC} | 50 °C/W |
| T_{SOLD} | 5.0 Sec./200 °C |


CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|----------------|--|---------|---------|------------|-------|
| V _B | I _R = 10 μA | 100 | | | V |
| C _J | V _R = 6.0 V f = 1.0 MHz | | | 0.05 | pF |
| R _S | I _F = 20 mA I _F = 100 mA f = 1.0 GHz | | | 2.6 2.0 | Ohms |
| T _L | I _F = 10 mA I _R = 6.0 mA | | 100 | | nS |
| T _S | 10%-90% / 90%-10% | | | 10 | nS |
| C _P | f = 1.0 MHz | | 0.15 | | pF |
| L _S | | | 2.5 | | nH |